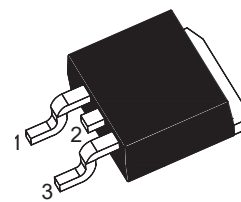
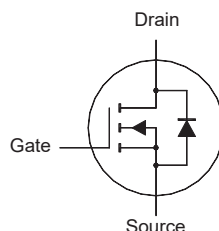


N-Channel Enhancement Mode MOSFET

Features

- Surface-mounted package
- 100% Avalanche tested
- Halogen and Antimony Free(HAF), RoHS compliant
- Typical ESD Protection HBM Class 2

Classification	Voltage Range(V)
0A	< 125
0B	125 to < 250
1A	250 to < 500
1B	500 to < 1000
1C	1000 to < 2000
2	2000 to < 4000
3A	4000 to < 8000
3B	≥ 8000



1.Gate 2.Drain 3.Source
TO-263 Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DS}	40	V
$R_{DS(ON)}$ Max	1.1 @ $V_{GS} = 10$ V	mΩ
$V_{GS(th)}$ typ	3	V
Q_g typ	141 @ $V_{GS} = 10$ V	nC

Absolute Maximum Ratings(at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_c = 25^\circ\text{C}$ 200 $T_c = 100^\circ\text{C}$ 126	A
Peak Drain Current, Pulsed ¹⁾	I_{DM}	800	A
Avalanche Current	I_{AS}	109	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	596	mJ
Power Dissipation	P_D	$T_c = 25^\circ\text{C}$ 106	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.41	°C/W
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	35	°C/W

¹⁾ Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 2%, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 175^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1$ mH, $R_g = 25$ Ω, $I_{AS} = 109$ A, $V_{GS} = 10$ V, $V_{DD} = 32$ V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 10\text{ mA}$	BV_{DSS}	40	-	-	V
Drain-Source Leakage Current at $V_{DS} = 40\text{ V}$ at $V_{DS} = 32\text{ V}$	I_{DSS}	- -	- -	10 1	μA
Gate Leakage Current at $V_{GS} = \pm 16\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$	$R_{DS(on)}$	-	0.9	1.1	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 5\text{ V}$, $I_D = 50\text{ A}$	g_{fs}	-	75	-	S
Gate Resistance at $V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ V}$, $f = 1\text{ MHz}$	R_g	-	2.2	-	Ω
Input Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 20\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	8793	-	pF
Output Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 20\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	3927	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 20\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	215	-	pF
Gate charge total at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$	Q_g	-	141	-	nC
Gate to Source Charge at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$	Q_{gs}	-	43	-	nC
Gate to Drain Charge at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$	Q_{gd}	-	42	-	nC
Turn-On Delay Time at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$, $R_g = 3.3\text{ }\Omega$	$t_{d(on)}$	-	55	-	ns
Turn-On Rise Time at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$, $R_g = 3.3\text{ }\Omega$	t_r	-	119	-	ns
Turn-Off Delay Time at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$, $R_g = 3.3\text{ }\Omega$	$t_{d(off)}$	-	42	-	ns
Turn-Off Fall Time at $V_{DS} = 20\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$, $R_g = 3.3\text{ }\Omega$	t_f	-	41	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 1\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_S	-	-	200	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	800	A
Body Diode Reverse Recovery Time at $I_S = 50\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	80	-	ns
Body Diode Reverse Recovery Charge at $I_S = 50\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	113	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

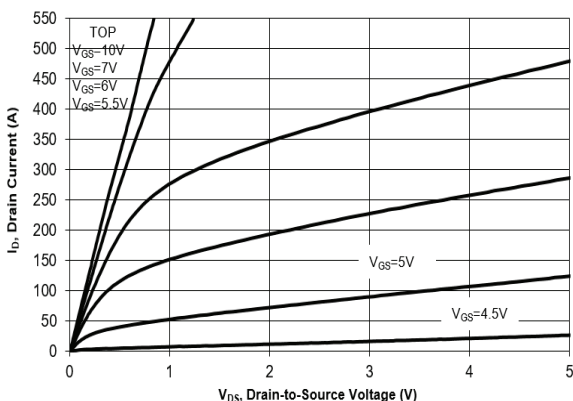


Fig. 2 Typical Transfer Characteristics

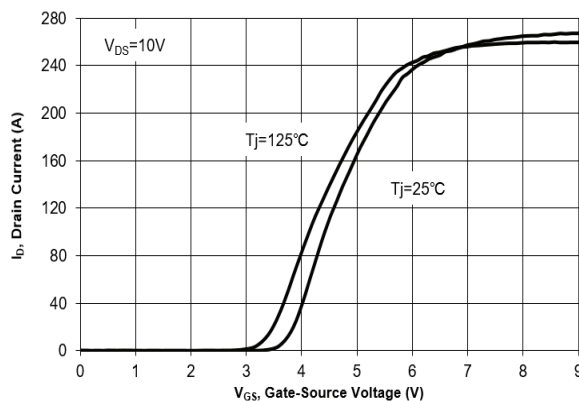


Fig. 3 On-Resistance vs. Drain Current

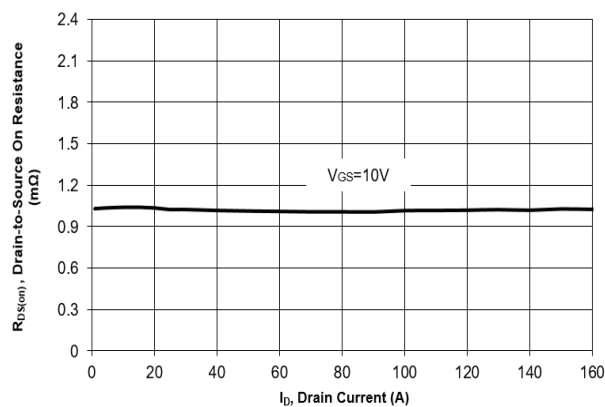


Fig. 4 On-Resistance vs. Gate to Source Voltage

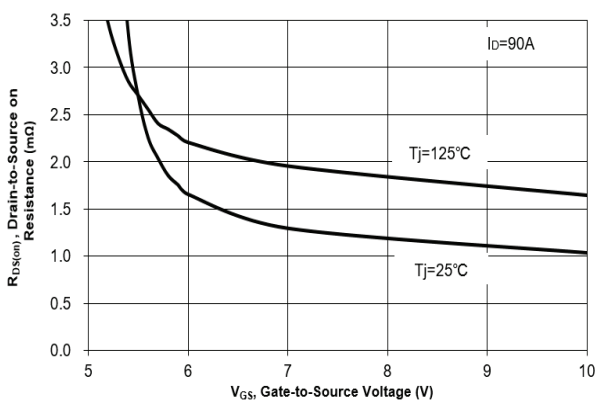


Fig. 5 On-Resistance vs. TJ

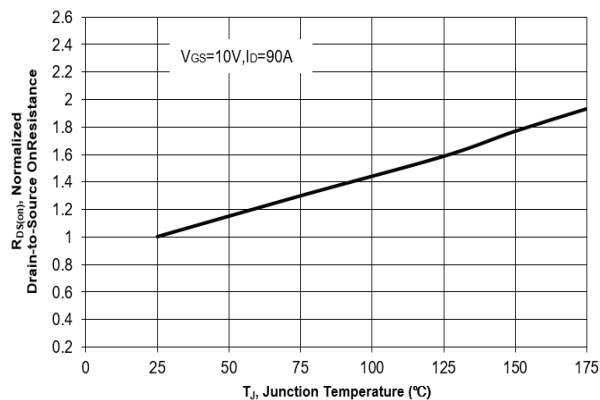
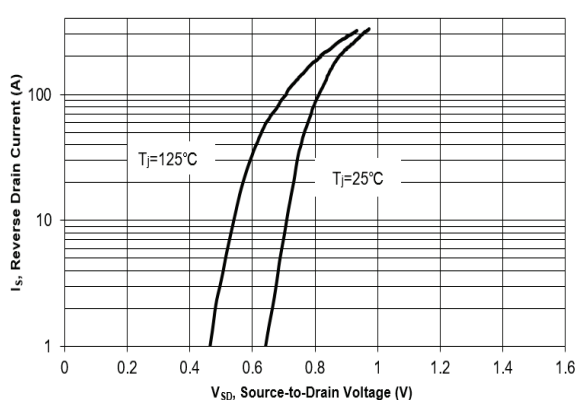


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

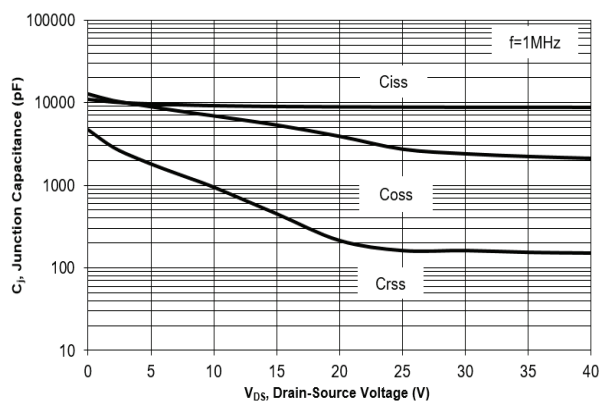


Fig. 8 Drain-Source Leakage Current vs. T_j

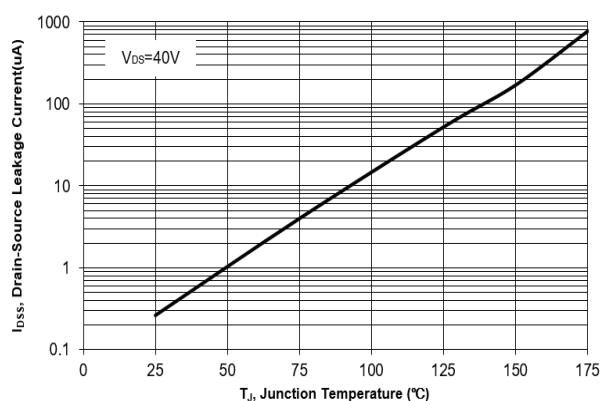


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

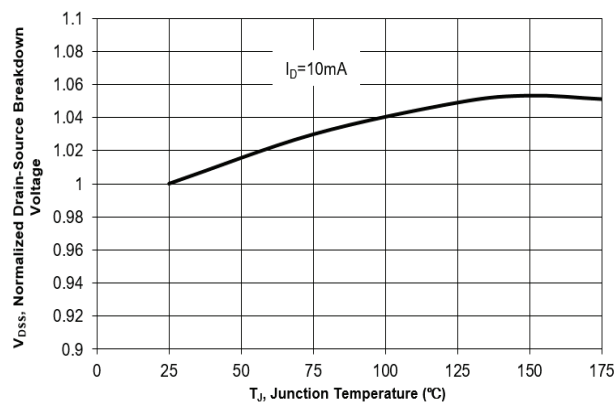


Fig. 10 Gate Threshold Variation vs. T_j

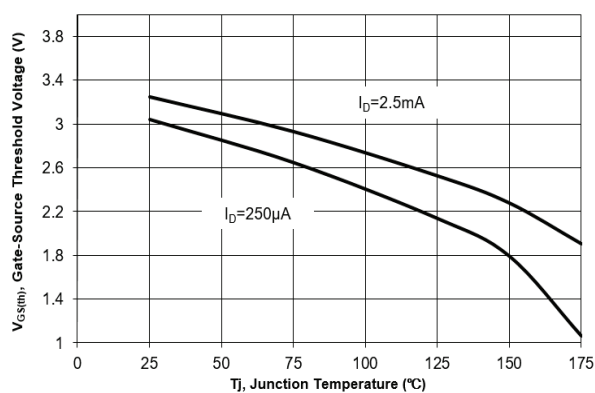


Fig. 11 Gate Charge

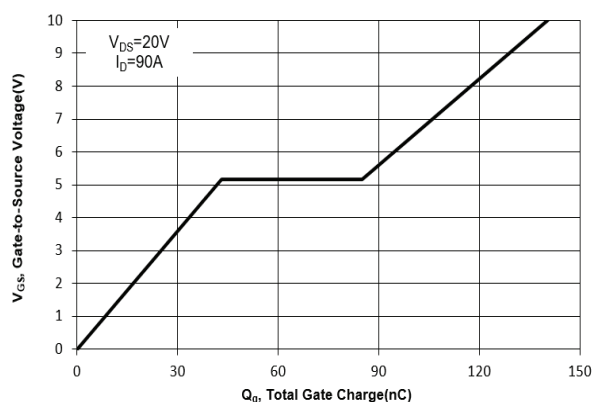
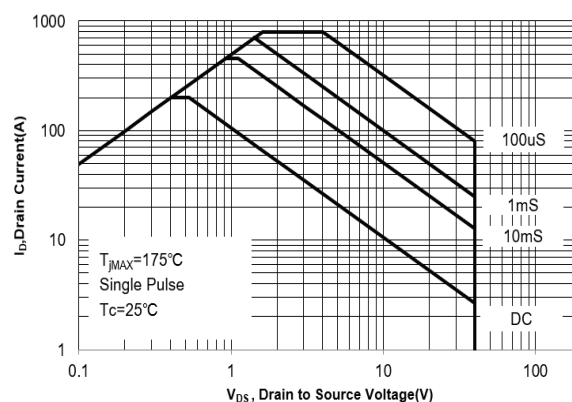


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

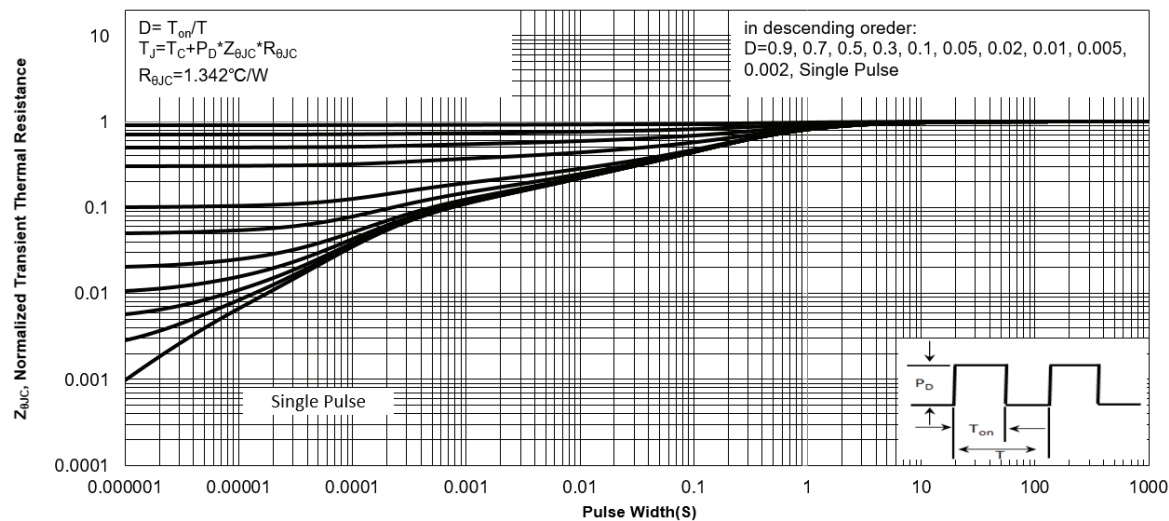
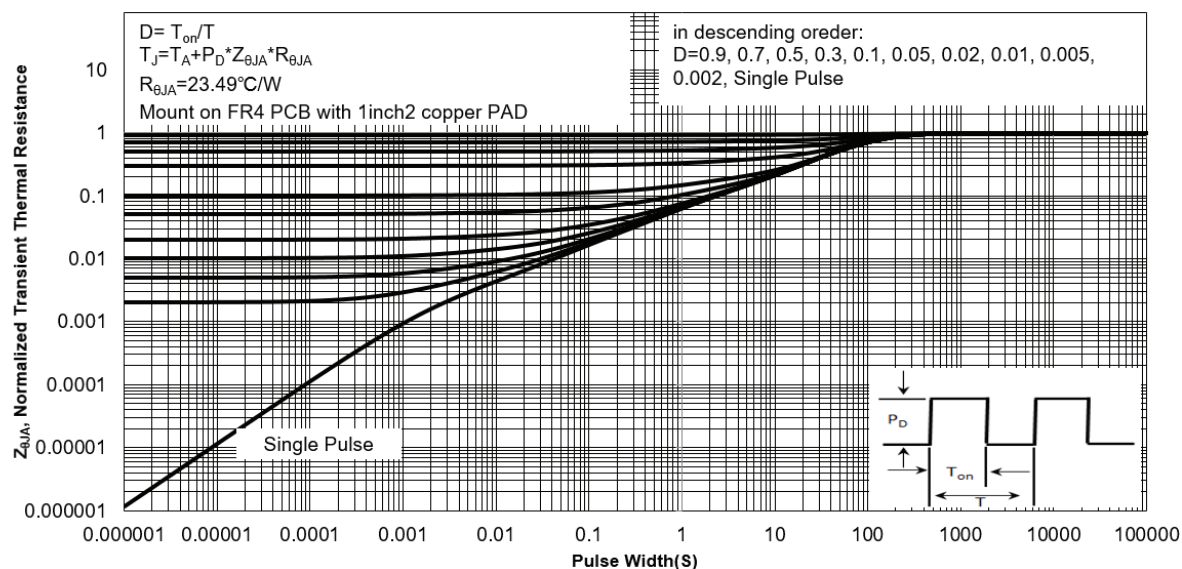
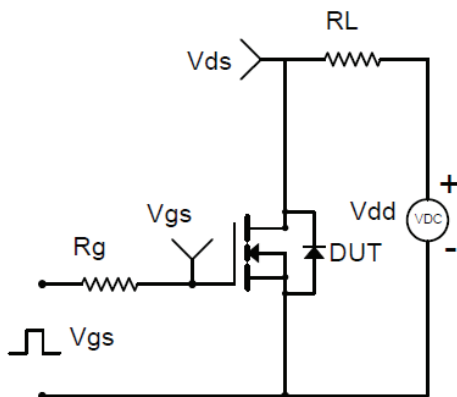
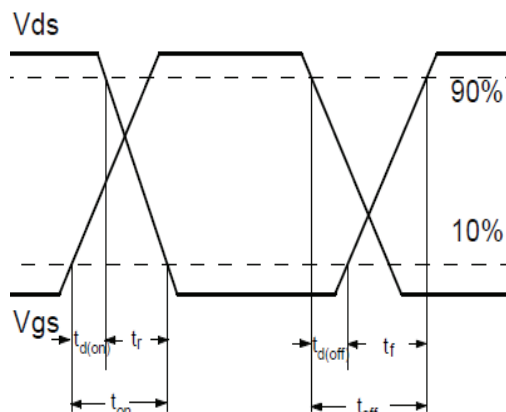
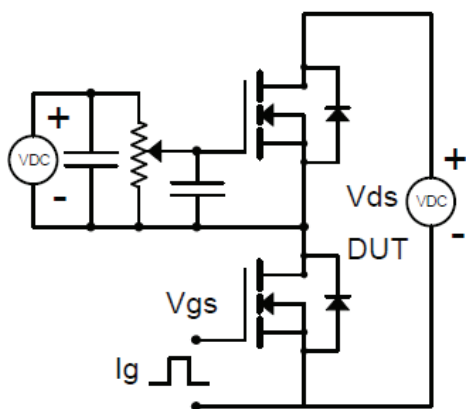
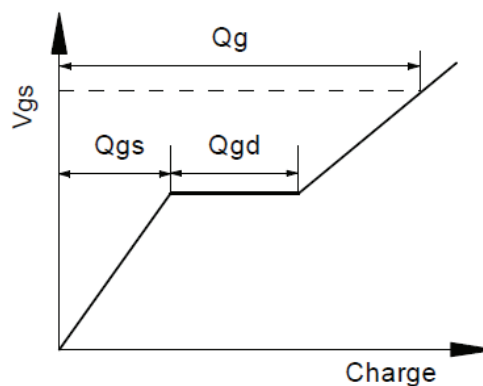
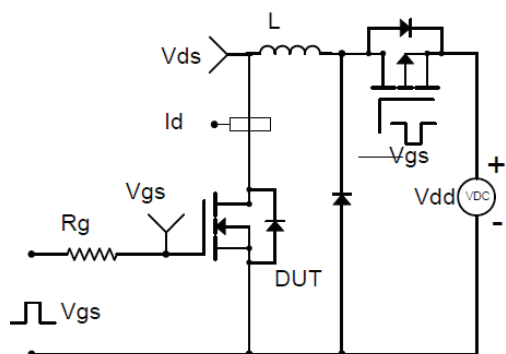
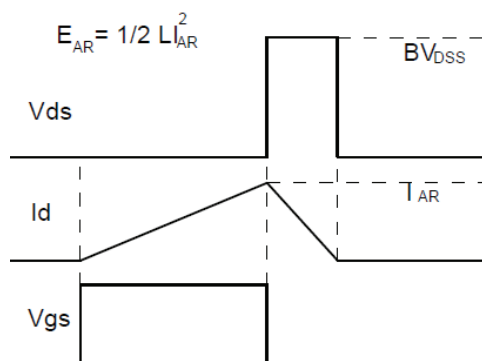
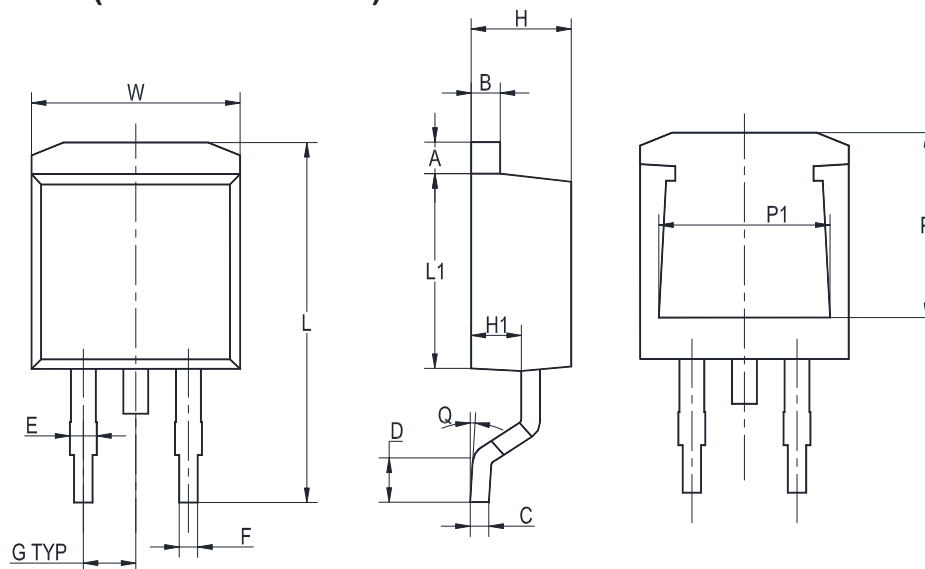


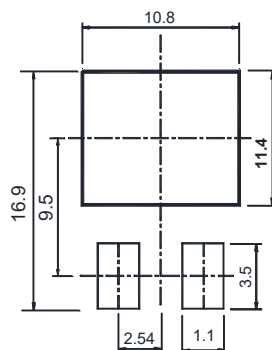
Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits
Fig.1-1 Switching times test circuit

Fig.1-2 Switching Waveform

Fig.2-1 Gate charge test circuit

Fig.2-2 Gate charge waveform

Fig.3-1 Avalanche test circuit

Fig.3-2 Avalanche waveform


Package Outline (Dimensions in mm)
TO-263


UNIT	A	B	C	D	E	F	G	W	H	H1	L	L1	Q	P	P1
mm	1.5	1.5	0.5	2.60	1.6	0.94	2.54	10.5	4.8	2.9	16.5	8.7	8°	7.6	8.2
	1.1	1.1	0.3	2.15	1.1	0.68	TYP	9.6	4.4	2.5	14.5	8.2	MAX	7.1	7.4

Recommended Soldering Footprint

Packing information

Package	Reel Quantity	Box Quantity	Carton Quantity	Delivery Mode
TO-263	0.8 K / Reel	0.8 K / Box	4K pcs / Carton	Reel

Marking information

" TV04N010L " = Part No.

" ***** " = Date Code Marking

Font type: Arial

